

Broduct data sheet

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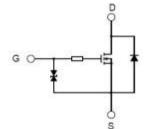
SOT-523

Specification Features:

- Low On-resistance
- Low Gate Threshold Voltage
- Low Input capacitance
- ESD Protected up to 1kV (HBM)
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:

Marking





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{DS}	Drain-Source Voltage	60	V	
V _{GS}	Continuous Gate-Source Voltage	± 20V	V	
١D	Continuous Drain Current	115	mA	
PD	Power Dissipation	150	mW	
Reja	Thermal Resistance from Junction to Ambient	833	°C /W	
T _{STG}	Storage Temperature Range	-55 to +150	°C	
TJ	Operating Junction Temperature	+150	°C	



Off Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
Symbol	Farameter	Test Condition	Min	Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =10uA	60			Volts
I _{GSS}	Gate-Body Leakage	V _{DS} =0V, V _{GS} =±20V			± 1	uA
ldss	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			100	nA

On Characteristics

Symphol	Parameter	Test Condition	Limits			Unit
Symbol	Farameter	Test Condition	Min	Тур	Max	Unit
Vth(GS)	Gate-Threshold Voltage	Vds= Vgs, Id=250uA	1		2.5	Volts
ID(ON)	On-state Drain Current	V _{GS} =10V, V _{DS} =7V	500			mA
RDS(on)	Drain-Source On-Resistance	V _{GS} =10V, I _D =300mA			2.8	Ω
		V _{GS} =4.5V, I _D =200mA			3	Ω
g fs	Forward Trans Conductance	V_{DS} =10V, I _D =200mA	80		500	ms
VDS(on)	Drain-Source On-Voltage	V_{GS} =10V, I _D =500mA			3.75	V
		V_{GS} =5V, I _D =50mA			0.375	V
Vsd	Diode Forward Voltage	I _S =250mA, V _{GS} =0V			1	V

Dynamic Characteristics

Symphol	Devenation	Test Condition	Limits			11
Symbol	Parameter		Min	Тур	Max	Unit
Ciss	Input Capacitance				50	pF
Coss	Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz			25	pF
Crss	Reverse Transfer Capacitance				5.0	pF

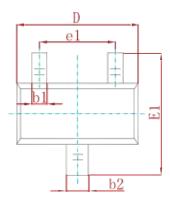
Switching Characteristics

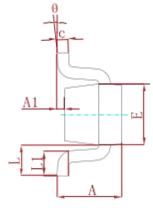
Symbol	Parameter	Test Condition		Limits		Unit
Symbol	Faiameter	Test Condition	Min	Тур	Max	Unit
t _{D(on)}	Turn-on Time	V_{DD} =10V, RL=20 Ω ,		5.6		nS
t _{D(off)}	Turn-off Time	I _D =500mA, V _{GEN} =10V, R _G = 10Ω		25		nS

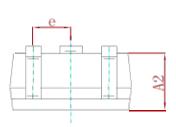




PACKAGE MECHANICAL DATA

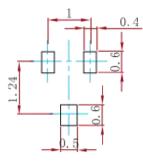






0 mm h a l	Dimensions I	Dimensions In Millimeters		s In Inches
Symbol	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
С	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500	TYP.	0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400	0.400 REF. 0.016 REF.		REF.
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters. 2.General tolerance:±0.05mm. 3.The pad layout is for reference purposes only.

3. The pad layout is for reference purposes or

REEL SPECIFICATION

P/N	PKG	QTY
2N7002KT	SOT-523	3000





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